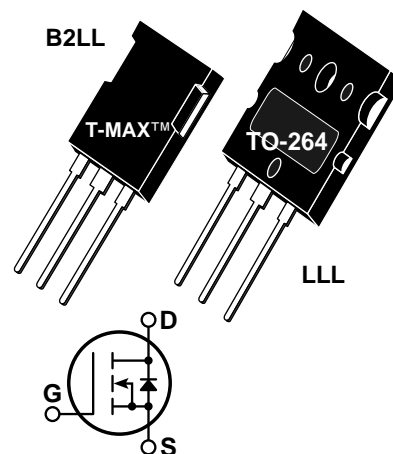


POWER MOS 7™

Power MOS 7™ is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETS. Both conduction and switching losses are addressed with Power MOS 7™ by significantly lowering $R_{DS(ON)}$ and Q_g . Power MOS 7™ combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.

- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge, Q_g
- Increased Power Dissipation
- Easier To Drive
- Popular T-MAX™ or TO-264 Package


MAXIMUM RATINGS

 All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

| Symbol | Parameter | APT20M16 | UNIT |
|----------------|---|------------|-------|
| V_{DSS} | Drain-Source Voltage | 200 | Volts |
| I_D | Continuous Drain Current @ $T_C = 25^\circ\text{C}$ ⑤ | 100 | Amps |
| I_{DM} | Pulsed Drain Current ① ⑤ | 400 | |
| V_{GS} | Gate-Source Voltage Continuous | ± 30 | Volts |
| V_{GSM} | Gate-Source Voltage Transient | ± 40 | |
| P_D | Total Power Dissipation @ $T_C = 25^\circ\text{C}$ | 690 | Watts |
| | Linear Derating Factor | 5.52 | W/°C |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to 150 | °C |
| T_L | Lead Temperature: 0.063" from Case for 10 Sec. | 300 | |
| I_{AR} | Avalanche Current ① (Repetitive and Non-Repetitive) | 100 | Amps |
| E_{AR} | Repetitive Avalanche Energy ① | 50 | mJ |
| E_{AS} | Single Pulse Avalanche Energy ④ | 3000 | |

STATIC ELECTRICAL CHARACTERISTICS

| Symbol | Characteristic / Test Conditions | MIN | TYP | MAX | UNIT |
|--------------|--|-----|-----|-----------|---------|
| BV_{DSS} | Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu A$) | 200 | | | Volts |
| $I_{D(on)}$ | On State Drain Current ② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$) | 100 | | | Amps |
| $R_{DS(on)}$ | Drain-Source On-State Resistance ② ($V_{GS} = 10V, 0.5 I_{D(Cont.)}$) | | | 0.016 | Ohms |
| I_{DSS} | Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$) | | | 100 | μA |
| | Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$) | | | 500 | |
| I_{GSS} | Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$) | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 2.5mA$) | 3 | | 5 | Volts |

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

| | | | | |
|---------------|--------------------------|---------------------------|---------------------------|-------------------------|
| USA | 405 S.W. Columbia Street | Bend, Oregon 97702-1035 | Phone: (541) 382-8028 | FAX: (541) 388-0364 |
| EUROPE | Chemin de Magret | F-33700 Merignac - France | Phone: (33) 5 57 92 15 15 | FAX: (33) 5 56 47 97 61 |

DYNAMIC CHARACTERISTICS

APT20M16 B2LL - LLL

| Symbol | Characteristic | Test Conditions | MIN | TYP | MAX | UNIT |
|--------------|--------------------------------|--|-----|------|-----|------|
| C_{iss} | Input Capacitance | $V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$ | | 7020 | | pF |
| C_{oss} | Output Capacitance | | | 2380 | | |
| C_{rss} | Reverse Transfer Capacitance | | | | 180 | |
| Q_g | Total Gate Charge ^③ | $V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[Cont.]} @ 25^\circ C$ | | 174 | | nC |
| Q_{gs} | Gate-Source Charge | | | 53 | | |
| Q_{gd} | Gate-Drain ("Miller") Charge | | | 96 | | |
| $t_{d(on)}$ | Turn-on Delay Time | $V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[Cont.]} @ 25^\circ C$ $R_G = 0.6\Omega$ | | 14 | | ns |
| t_r | Rise Time | | | 24 | | |
| $t_{d(off)}$ | Turn-off Delay Time | | | 29 | | |
| t_f | Fall Time | | | 7 | | |

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

| Symbol | Characteristic / Test Conditions | MIN | TYP | MAX | UNIT |
|----------|---|-----|-----|-----|---------|
| I_S | Continuous Source Current (Body Diode) | | | 100 | Amps |
| I_{SM} | Pulsed Source Current ^① (Body Diode) | | | 400 | |
| V_{SD} | Diode Forward Voltage ^② ($V_{GS} = 0V, I_S = -I_{D[Cont.]}$) | | | 1.3 | Volts |
| t_{rr} | Reverse Recovery Time ($I_S = -I_{D[Cont.]}, di_S/dt = 100A/\mu s$) | | 360 | | ns |
| Q_{rr} | Reverse Recovery Charge ($I_S = -I_{D[Cont.]}, di_S/dt = 100A/\mu s$) | | 6.7 | | μC |
| dv/dt | Peak Diode Recovery dv/dt ^⑥ | | | 5 | V/ns |

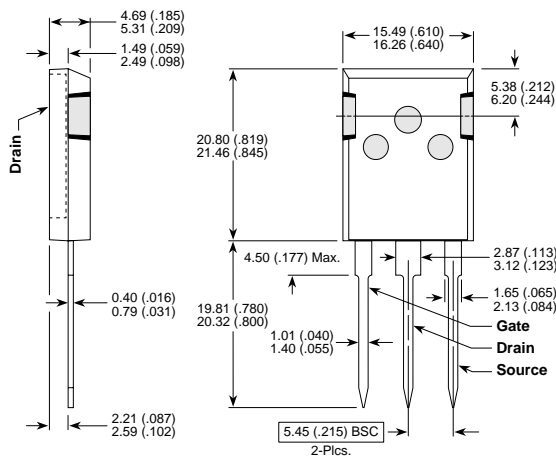
THERMAL CHARACTERISTICS

| Symbol | Characteristic | MIN | TYP | MAX | UNIT |
|-----------------|---------------------|-----|-----|------|--------------|
| $R_{\theta JC}$ | Junction to Case | | | 0.18 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction to Ambient | | | 40 | |

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%
- ③ See MIL-STD-750 Method 3471
- ④ Starting $T_j = +25^\circ C$, $L = .6mH$, $R_G = 25\Omega$, Peak $I_L = 100A$
- ⑤ The maximum current is limited by lead temperature
- ⑥ dv/dt numbers reflect the limitations of the test circuit rather than the device itself. $I_S \leq -I_{D[Cont.]}$ $di/dt \leq 700A/\mu s$ $V_R \leq V_{DSS}$ $T_j \leq 150^\circ C$

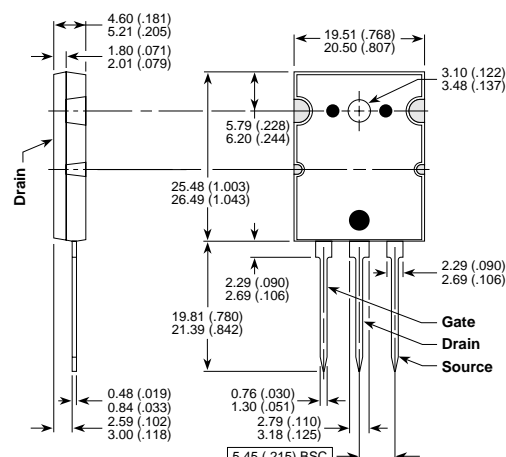
APT Reserves the right to change, without notice, the specifications and information contained herein.

T-MAX™ (B2) Package Outline



These dimensions are equal to the TO-247 without the mounting hole.
Dimensions in Millimeters and (Inches)

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)

APT's devices are covered by one or more of the following U.S. patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336
5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058